

Andrei Gloskovskii

List of Publications by Year in descending order

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30
papers

889
citations

623734

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h-index

526287

27
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30
all docs

30
docs citations

30
times ranked

1505
citing authors

#	ARTICLE	IF	CITATIONS
1	Time-resolved x-ray diffraction and photoelectron spectroscopy investigation of the reactive molecular beam epitaxy of FeO_4 ultrathin films. <i>Physical Review B</i> , 2022, 105, .	8.3	10
2	Real-Time Monitoring the Growth of Epitaxial CoFe_3O_4 Ultrathin Films on Nb-Doped $\text{SrTiO}_3(001)$ via Reactive Molecular Beam Epitaxy by Means of Operando HAXPES. <i>Materials</i> , 2022, 15, 2377.	2.9	0
3	Standing wave hard X-ray photoemission study of the structure of the interfaces in Ta/Co ₂ FeAl/MgO multilayer. <i>Applied Surface Science</i> , 2022, 590, 153063.	6.1	3
4	Surface resonance of thin films of the Heusler half-metal Co_2MnSi probed by soft x-ray angular resolved photoemission spectroscopy. <i>Physical Review B</i> , 2019, 99, .	3.2	10
5	Tunable Magnetic Phases at $\text{Fe}_3\text{O}_4/\text{SrTiO}_3$ Oxide Interfaces. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 7576-7583.	8.0	17
6	Polarization-dependent electric potential distribution across nanoscale ferroelectric $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ in functional memory capacitors. <i>Nanoscale</i> , 2019, 11, 19814-19822.	5.6	11
7	Role of antisite disorder, electron-electron correlations, and a surface valence transition in the electronic structure of CeMnNi_4 . <i>Physical Review B</i> , 2019, 99, .	3.2	10
8	Operando diagnostic detection of interfacial oxygen "breathing" of resistive random access memory by bulk-sensitive hard X-ray photoelectron spectroscopy. <i>Materials Research Letters</i> , 2019, 7, 117-123.	8.7	19
9	Signature of a highly spin polarized resonance state at $\text{Co}_2\text{MnSi}/\text{Ag}$ interfaces. <i>Journal Physics D: Applied Physics</i> , 2018, 51, 135307.	2.8	4
10	Effect of Polarization Reversal in Ferroelectric $\text{TiN}/\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2/\text{TiN}$ Devices on Electronic Conditions at Interfaces Studied in Operando by Hard X-ray Photoemission Spectroscopy. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 43370-43376.	8.0	46
11	Accurate determination of the valence band edge in hard x-ray photoemission spectra using CW theory. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	5
12	Spectroscopic fingerprints for charge localization in the organic semiconductor (DOEO) ₄ [HgBr ₄]·TCE. <i>European Physical Journal B</i> , 2015, 88, 1.	1.5	0
13	Hard X-ray photoemission study of the Fabre salts (TMTTF) ₂ X (X = SbF ₆ and PF ₆). <i>European Physical Journal B</i> , 2014, 87, 1.	1.5	11
14	Engineering of the Chemical Reactivity of the Ti/HfO_2 Interface for RRAM: Experiment and Theory.. <i>ACS Applied Materials & Interfaces</i> , 2014, 6, 5056-5060.	8.0	55
15	Optimum Carrier Concentration in n-type PbTe Thermoelectrics. <i>Advanced Energy Materials</i> , 2014, 4, 1400486.	19.5	348
16	Electronic structure and optical, mechanical, and transport properties of the pure, electron-doped, and hole-doped Heusler compound CoTiSb . <i>Physical Review B</i> , 2012, 86, .	3.2	49
17	A p-type Heusler compound: Growth, structure, and properties of epitaxial thin NiYBi films on $\text{MgO}(100)$. <i>Applied Physics Letters</i> , 2012, 101, 212102.	3.3	11
18	In-operando and non-destructive analysis of the resistive switching in the $\text{Ti}/\text{HfO}_2/\text{TiN}$ -based system by hard x-ray photoelectron spectroscopy. <i>Applied Physics Letters</i> , 2012, 101, 143501.	3.3	59

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19	Structure determination of thin CoFe films by anomalous x-ray diffraction. Journal of Applied Physics, 2012, 112, 074903.	2.5	4
20	Magnetometry of buried layers—Linear magnetic dichroism and spin detection in angular resolved hard X-ray photoelectron spectroscopy. Journal of Electron Spectroscopy and Related Phenomena, 2012, 185, 47-52.	1.7	56
21	Investigation of the Thermoelectric Properties of the Series $TiCo_{1-x}Ni_xSn_xSb_{1-x}$. Zeitschrift Fur Anorganische Und Allgemeine Chemie, 2010, 636, 132-136.	1.2	5
22	Magnetic and Structural Properties of Heusler Compounds with 27.8 Valence Electrons. Zeitschrift Fur Anorganische Und Allgemeine Chemie, 2010, 636, 966-971.	1.2	2
23	Electronic properties of Co_2MnSi thin films studied by hard x-ray photoelectron spectroscopy. Journal Physics D: Applied Physics, 2009, 42, 084011.	2.8	10
24	Hard x-ray photoelectron spectroscopy of buried Heusler compounds. Journal Physics D: Applied Physics, 2009, 42, 084010.	2.8	18
25	Thermoelectric properties of $CoTiSb$ based compounds. Journal Physics D: Applied Physics, 2009, 42, 185401.	2.8	34
26	Doped semiconductors as half-metallic materials: Experiments and first-principles calculations of $Co_{1-x}Ti_x$		